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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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## Silicon Carbide Thyristor

$V_{FBM}$	=	6500 V
$I_{T(AVM)}$	=	80 A
$Q_{rr}$	=	4.2 $\mu$ C

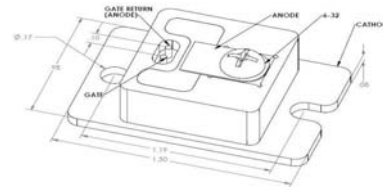
### Features

- 6500 V Asymmetric SiC NPNP Thyristor
- 150 °C operating temperature
- Robust compact fully soldered package
- SOT-227 (ISOTOP) base plate form factor
- Fast turn on characteristics
- Lowest in class  $Q_{rr}/I_{T(AVM)}$

### Applications

- Grid Tied Solar Inverters
- Wind Power Inverters
- HVDC Power Conversion
- Utility Scale Power Conversion
- Trigger Circuits/Ignition Circuits

### Package



### Maximum Ratings

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak forward voltage	$V_{FBM}$	$T_j = 25\text{ }^\circ\text{C}$	6500	V
Repetitive peak reverse voltage	$V_{RBM}$	$T_j = 25\text{ }^\circ\text{C}$	50	V
Maximum average on-state current	$I_{T(AVM)}$	$T_c \leq 125\text{ }^\circ\text{C}$	80	A
RMS on-state current	$I_{T(RMS)}$	$T_c \leq 125\text{ }^\circ\text{C}$	139	A
Non-repetitive peak on-state current	$I_{T,max}$	$T_c = 25\text{ }^\circ\text{C}$ , $t_p = 2\text{ }\mu\text{s}$ , $D = 0.1$	tdb	A
Power dissipation	$P_{tot}$	$T_c = 25\text{ }^\circ\text{C}$	1563	W
Operating and storage temperature	$T_j, T_{stg}$		-55 to 150	$^\circ\text{C}$

### Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Maximum peak on state voltage	$V_{KA(ON)}$	$I_K = -80\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$ $I_K = -80\text{ A}$ , $T_j = 150\text{ }^\circ\text{C}$		-3.70 -3.45		V
Anode-cathode threshold voltage	$V_{KA(TO)}$	$T_j = 25\text{ }^\circ\text{C}$ (150 °C)		-3.0(-2.7)		V
Anode-cathode slope resistance	$R_{AK}$	$T_j = 25\text{ }^\circ\text{C}$ (150 °C), $I_K = -80\text{ A}$		6.0(6.3)		m $\Omega$
Leakage current	$I_L$	$V_{KA} = -6500\text{ V}$ , $V_{GA} = 0\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$ $V_{KA} = -6500\text{ V}$ , $V_{GA} = 0\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$		15 50		$\mu$ A
Gate trigger current	$I_{GT}$	$T_j = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ }\mu\text{s}$		-100		mA
Holding current	$I_H$	$T_j = 25\text{ }^\circ\text{C}$		tdb		mA
Rise time	$t_R$	$I_G = -3\text{ A}$ , $V_{KA} = -2200\text{ V}$		190		ns
Delay time	$t_D$	$I_K = -80\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$		50		ns
Reverse recovery charge	$Q_{rr}$			4.2		$\mu$ C
Recovered charge, 50% chord	$Q_{ra}$	$dI/dt = 430\text{ A}/\mu\text{s}$ , $I_K = -70\text{ A}$ , $V_{KA} = 20\text{ V}$		2.3		$\mu$ C
Reverse recovery current	$I_{rm}$	$dV/dt(\text{re-app}) = -460\text{ V}/\mu\text{s}$ , $T_j = 25\text{ }^\circ\text{C}$		20		A
Circuit commutated turn-off time	$t_q$			10.1		$\mu\text{s}$

### Thermal Characteristics

Thermal resistance, junction - case	$R_{thJC}$	0.08	$^\circ\text{C}/\text{W}$
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### Mechanical Properties

Mounting torque for base	$M_b$	Heat sink surface must be optically flat	1.5	Nm
Mounting torque for top	$M_t$		1.3	Nm
Weight	$W_t$		30	g

1. Considering worst case  $Z_{th}$  conditions

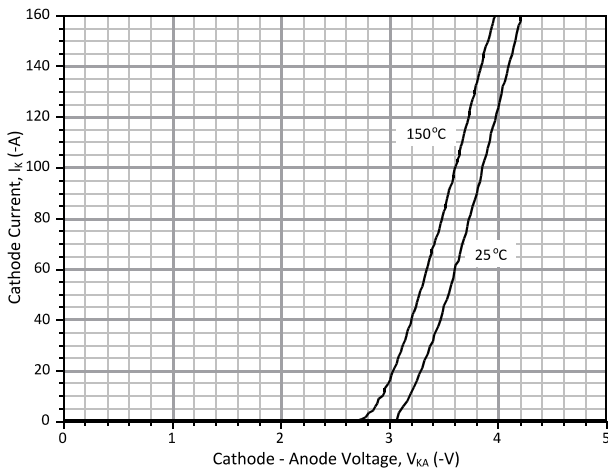


Figure 1: Typical On State Characteristics

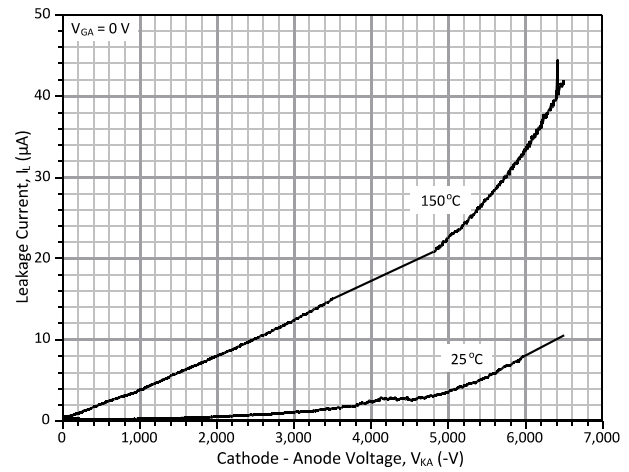


Figure 2: Typical Forward Blocking Characteristics

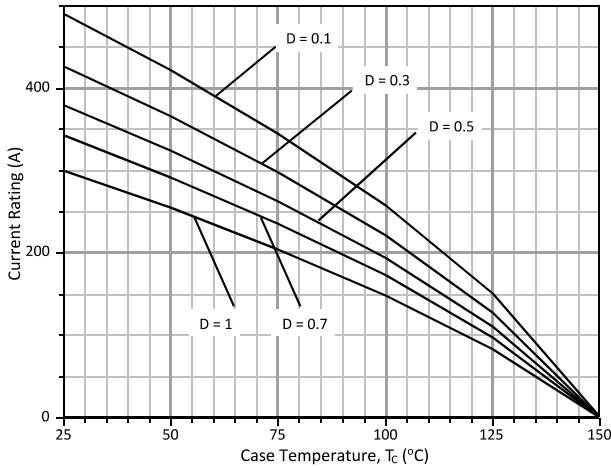


Figure 3: Typical Current Derating Curves ( $D = t_p/T, t_p = 400 \mu s$ )

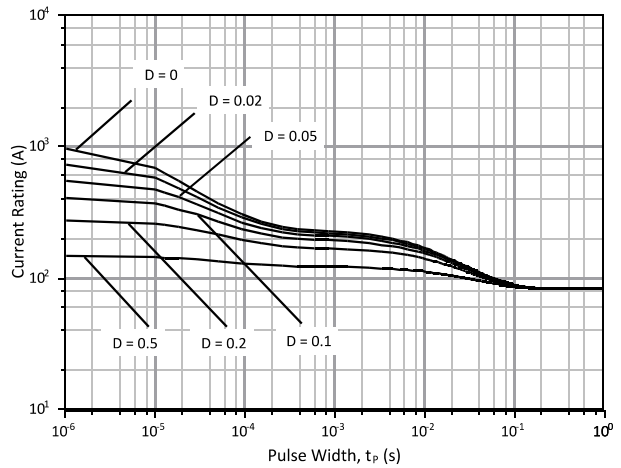


Figure 4: Typical Current Rating versus Pulse Duration Curves at  $T_c = 120 \text{ }^\circ\text{C}$

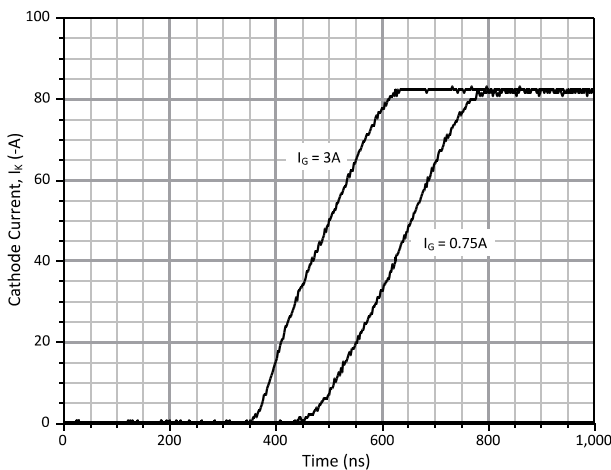


Figure 5: Typical Turn On Characteristics at 25 °C

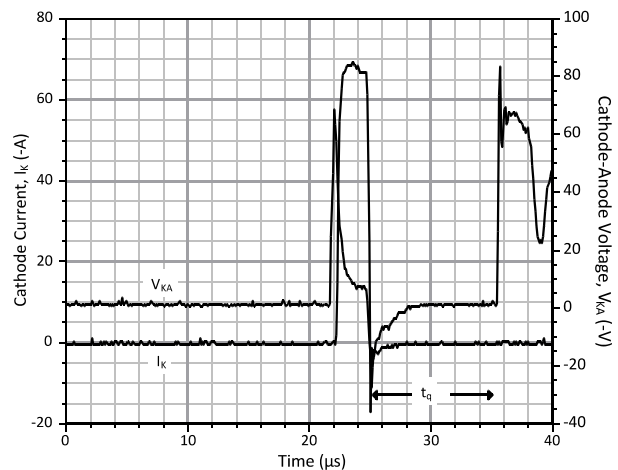


Figure 6: Typical Turn Off Characteristics at 25 °C

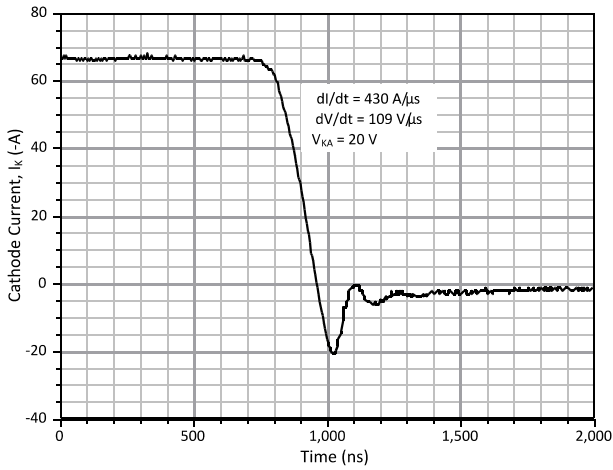


Figure 7: Typical Reverse Recovery Characteristics at 25 °C

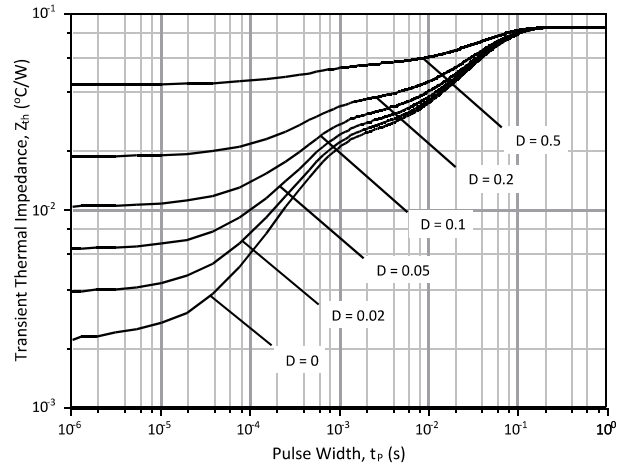


Figure 8: Typical Transient Thermal Impedance

**Revision History**

Date	Revision	Comments	Supersedes
2010/11/13	1	First generation release	

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